

FORM 1449*	INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION <small>(Use several sheets if necessary)</small>	
	Docket Number: STFD.036US	Application Number: 10/518,779
	Applicant: GOPALAKRISHNAN et al.	
	Filing Date: 12/17/2004	Group Art Unit: Unassigned

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
				*			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

OTHER DOCUMENTS (including Author, Title, Date, Citation Index, etc.)	
12/1980	J. Plummer, B. Scharf. "Insulated-Gate Planar Thyristors: I-Structure and Basic Operation." <i>IEEE Transactions on Electron Devices</i> , Vol. ED-27, No. 2. February 1980. pp. 380-386. BEST COPY AVAILABLE
01/1976	M. Declercq and J. Plummer. "Avalanche Breakdown in High-Voltage D-MOS Devices." <i>IEEE Transactions on Electron Devices</i> , Vol. ED-23, No. 1. January 1976. pp. 1-4. BEST COPY AVAILABLE
9/17/1997	Z.S. Gribnikov et al. "The Tunnel Diode as a Thyristor Emitter." <i>Solid-State Electronics</i> , Vol. 42, No. 9. 17 September 1997. pp 1761-1763. BEST COPY AVAILABLE
11/1998	D. M. Kim. "Electrical Characteristics of Npn-AlGaAs/GaAs HBTs with Modulated Base Doping Structures." <i>Journal of the Korean Physical Society</i> , Vol. 33, No. 5. November 1998. pp. 607-611.

EXAMINER	/Sarah Salerno/	DATE CONSIDERED	/S.K.S./
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not relied upon			

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